

FIG. 1

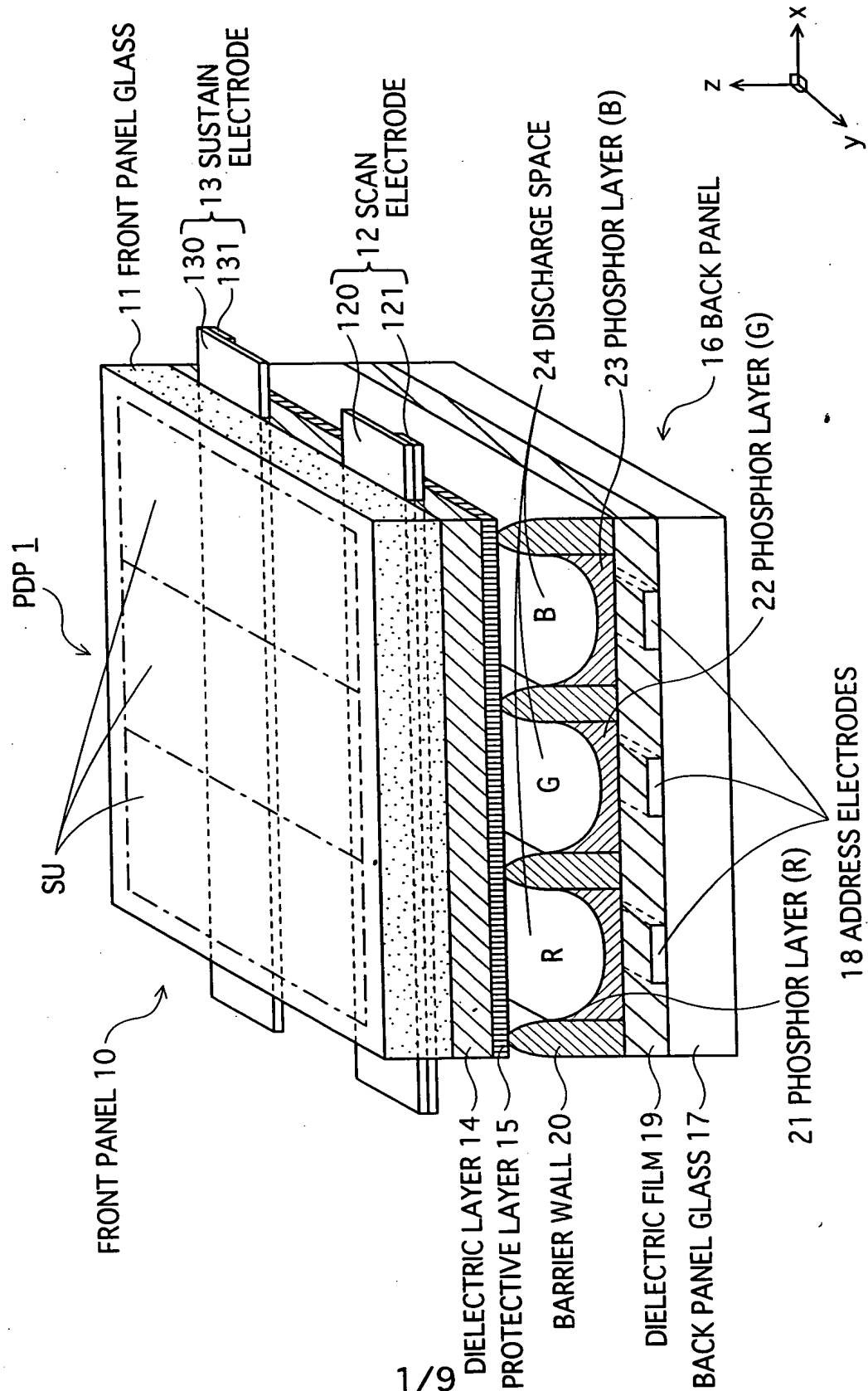


FIG. 2

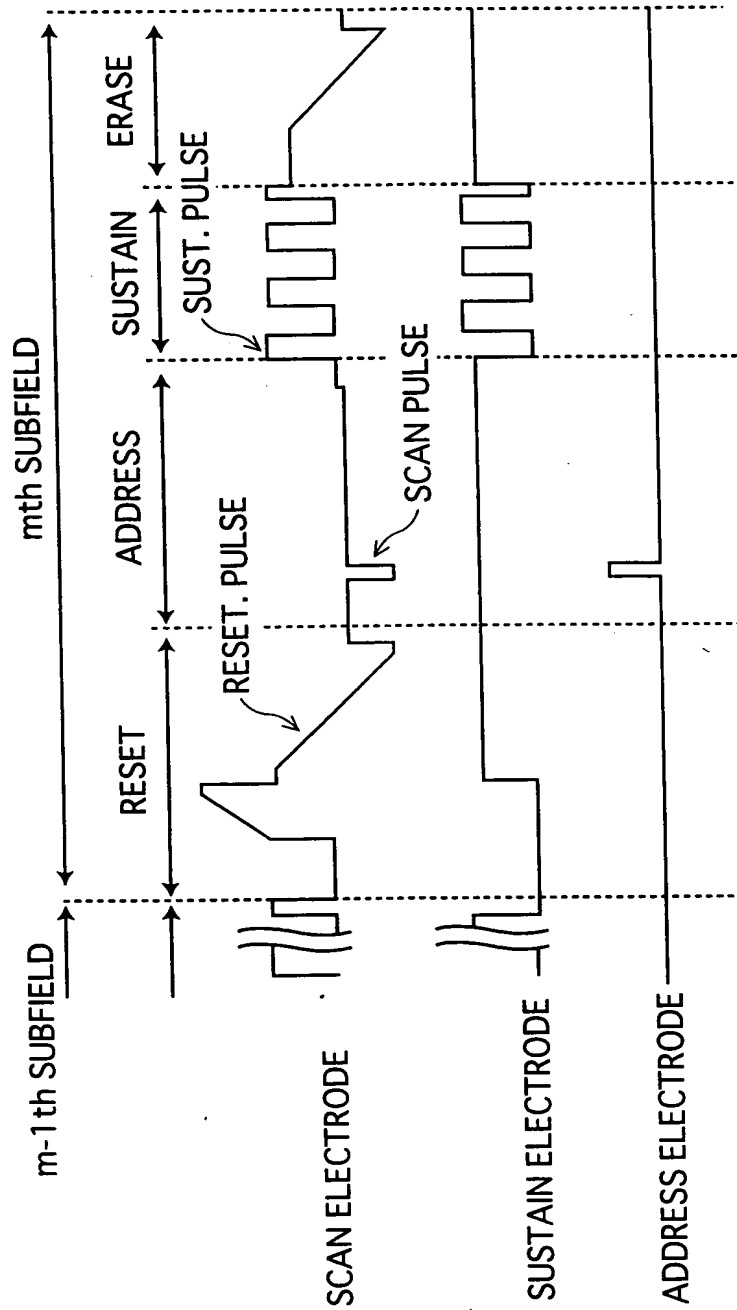


FIG.3

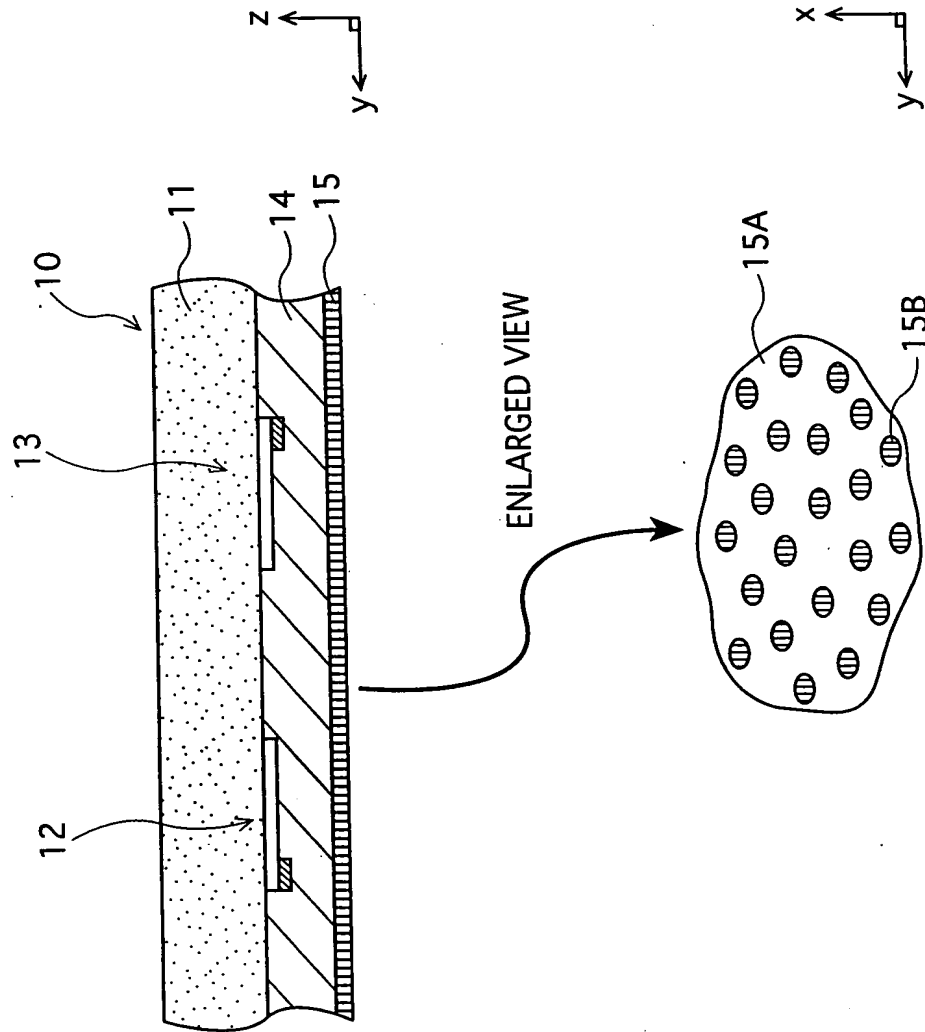




FIG.5

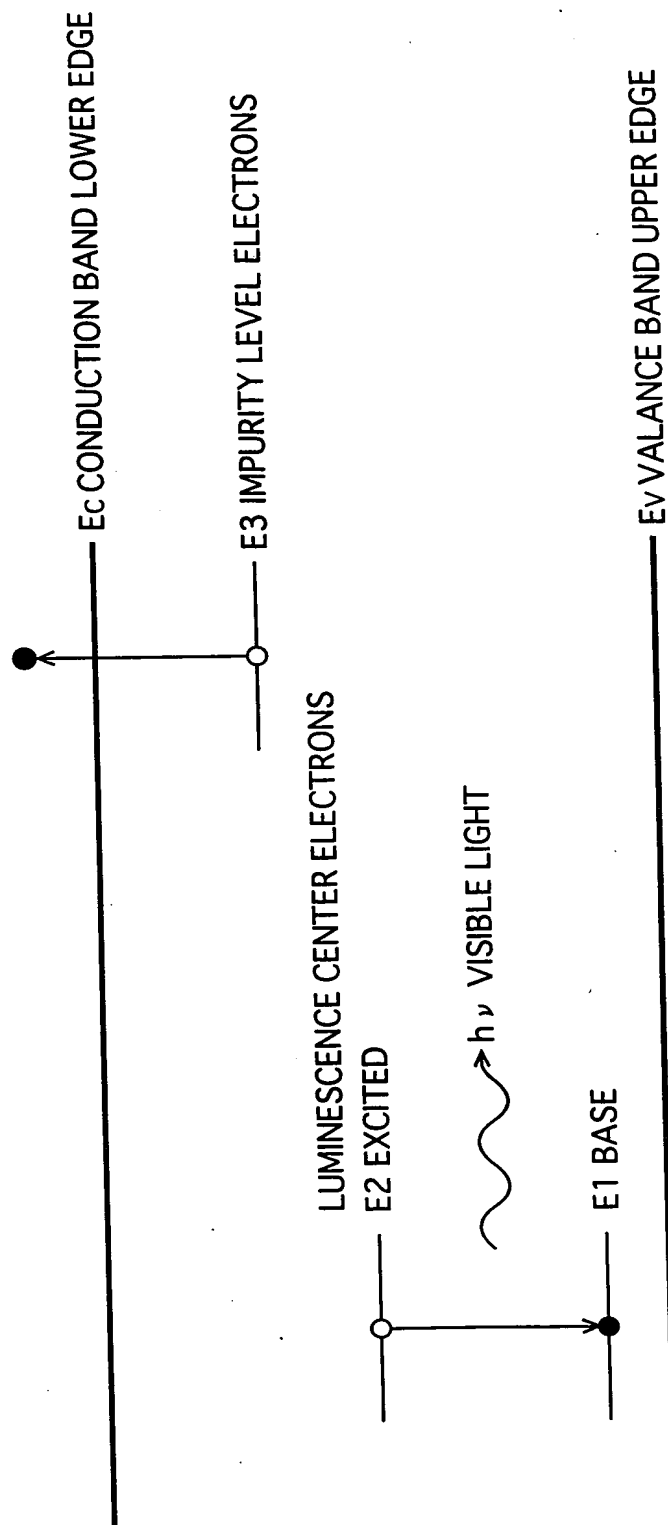


FIG. 6A

A detailed cross-sectional view of a semiconductor device 1 along a line a-a'. The device consists of several layers: a top layer 11 with a dotted pattern; a thin layer 120; another thin layer 121; a layer 14 with a horizontal line pattern; a layer 15 with a vertical line pattern; a layer 19 with a diagonal line pattern; and a bottom layer 17. A series of rectangular blocks 20 are embedded in the bottom layer 17. Above these blocks, a layer 18 contains a series of curved, shaded regions 24. A layer 150 is located above the curved regions 24. A dashed line a-a' indicates the cross-section. A coordinate system with z and y axes is shown in the bottom right corner.

FIG.7

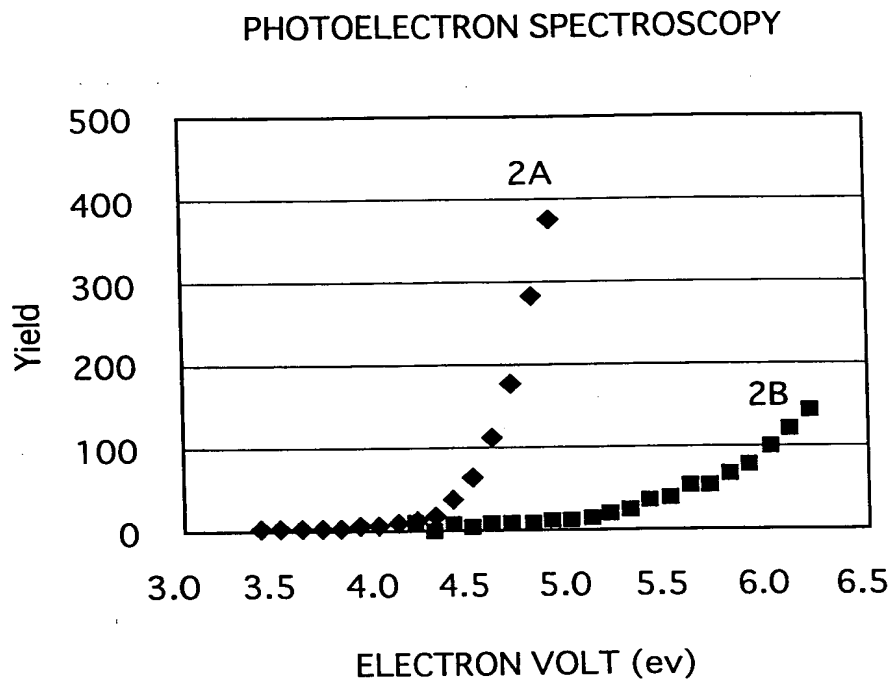


FIG.8

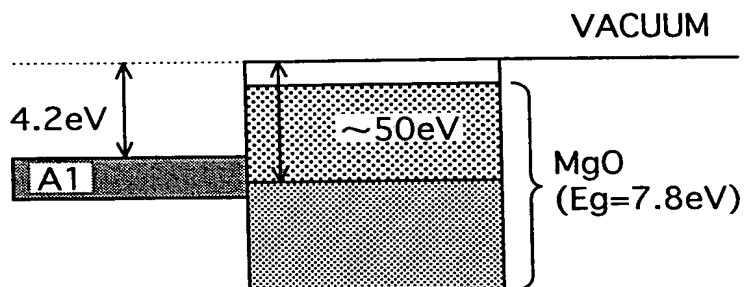


FIG.9A

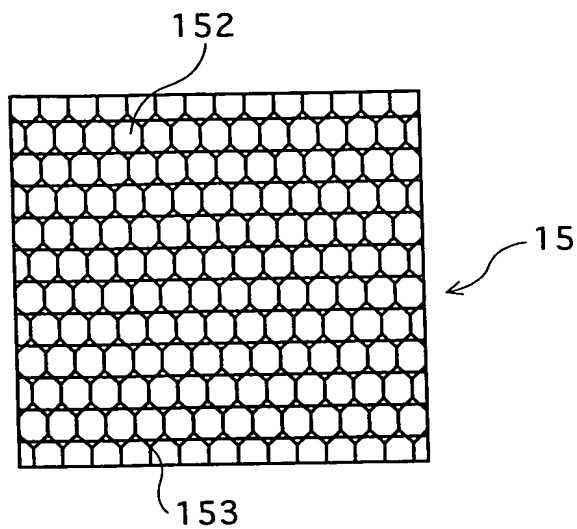
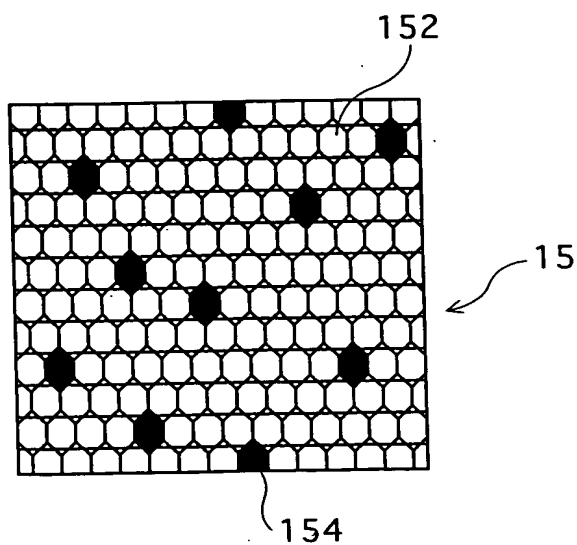


FIG.9B



A detailed cross-sectional diagram of a semiconductor device 1. The device consists of several layers: a top layer 11; a middle section 12 containing layers 120 and 121; a layer 14; a layer 15; a substrate 19; and a bottom layer 17. A patterned layer 18 is formed on the substrate 19, featuring rectangular openings 20. A layer 24 is located above the substrate 19, containing semi-circular features 155. A dashed vertical line indicates a plane of symmetry or measurement, with arrows labeled 'a' at the top and 'a'' at the bottom. A coordinate system in the bottom right corner shows a vertical 'z' axis and a horizontal 'y' axis.